

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	19mΩ @ V _{GS} = 10V	33.2A
00 v	28mΩ @ V _{GS} = 4.5V	28A

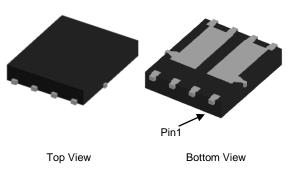
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

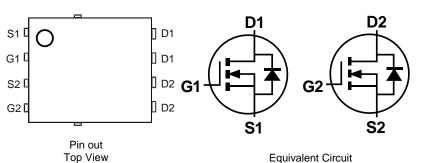
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters



Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🕄
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 5)

	Part Number	Case	Packaging			
	DMTH6016LPDQ-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel			
Notes:	tes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.					

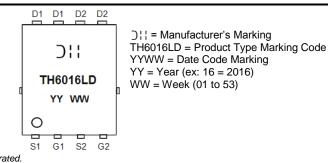
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



PowerDI is a registered trademark of Diodes Incorporated. DMTH6016LPDQ Document number: DS39429 Rev. 2 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7)	T _C = +25°C T _C = +100°C	ID	33.2 23.7	А
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +100°C	ID	9.2 6.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	50	А	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	31	А	
Pulsed Body Diode Forward Current (Note 6)	I _{SM}	50	А	
Avalanche Current, L = 0.1mH		I _{AS}	15.3	A
Avalanche Energy, L = 0.1mH		Eas	11.7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{OJA}	58	°C/W	
Total Power Dissipation (Note 7)	PD	37.5	W	
Thermal Resistance, Junction to Case (Note 7)		R _{ØJC}	4	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

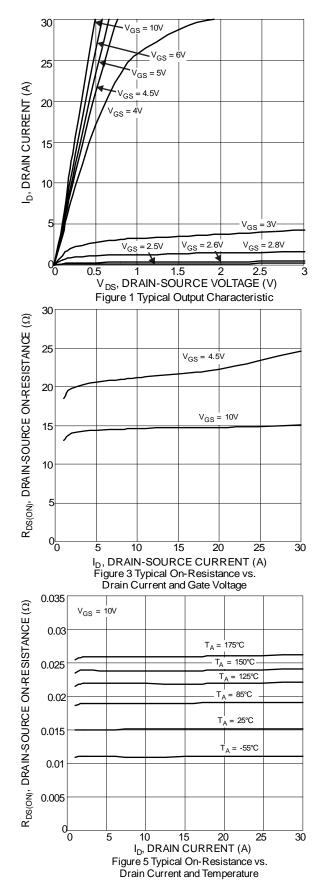
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			- 71-				
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	—	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Р	_	14.5	19	mΩ	V _{GS} = 10V, I _D = 10A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	20.9	28	mΩ	$V_{GS} = 4.5 V, I_D = 6 A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)				•	•	•	
Input Capacitance	CISS	_	864	—	pF	$V_{DS} = 30V, V_{GS} = 0V,$ - f = 1MHz	
Output Capacitance	C _{OSS}	—	282	_	pF		
Reverse Transfer Capacitance	C _{RSS}	_	27	—	pF		
Gate Resistance	R _G	_	1.3	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G		8.4	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q _G		17	_	nC		
Gate-Source Charge	Q _{GS}	_	3.1	—	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Q _{GD}	_	4.3	—	nC	7	
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns	V _{DD} = 30V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	_	5.2	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	13	—	ns	$I_D = 10A, R_G = 6\Omega$	
Turn-Off Fall Time	tF	_	7	_	ns	7	
Body Diode Reverse Recovery Time	t _{RR}	_	22	_	ns	I _F = 10A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	11	_	nC		

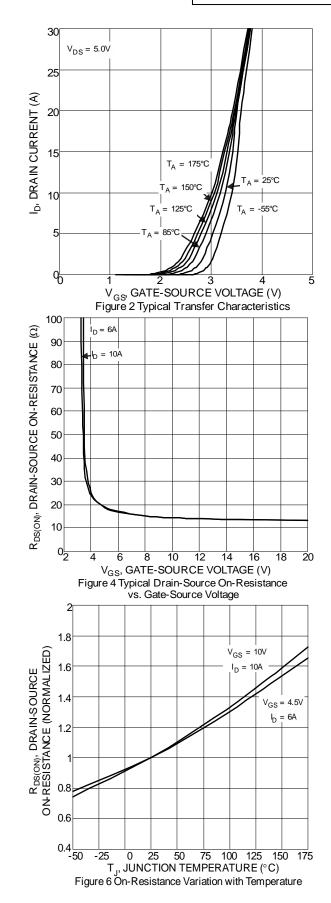
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect. Notes:

9. Guaranteed by design. Not subject to product testing.



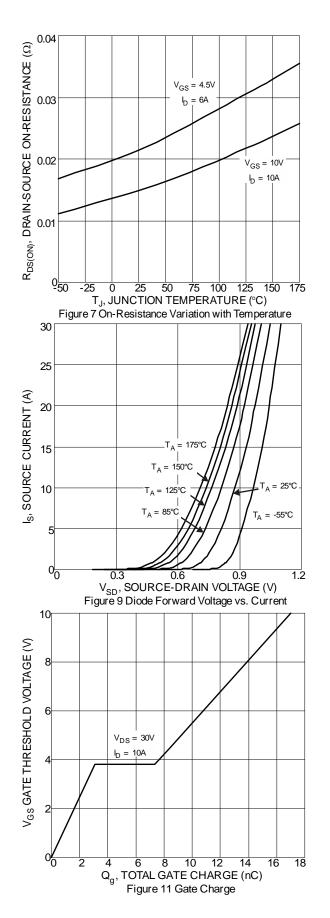
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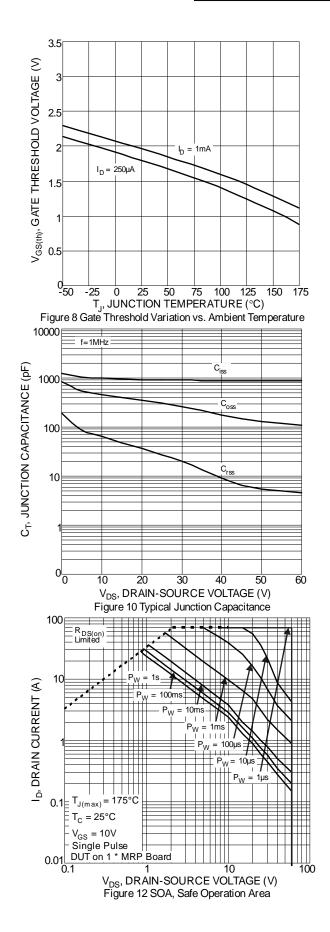




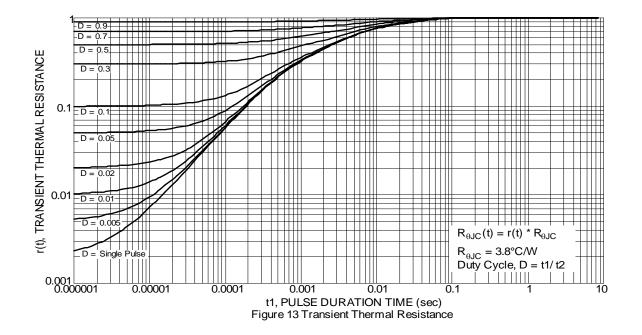
DMTH6016LPDQ Document number: DS39429 Rev. 2 - 2







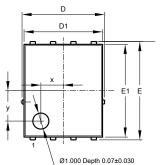


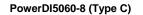


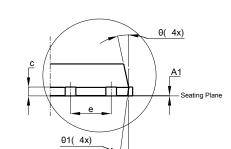


Package Outline Dimensions

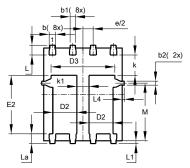
Please see http://www.diodes.com/package-outlines.html for the latest version.

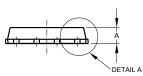










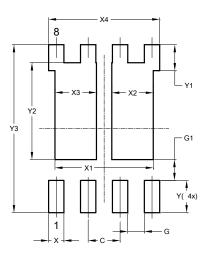


Po	PowerDI5060-8 (Type C)						
Dim	Min	Тур					
Α	0.90	1.10	1.00				
A1	0	0.05	0.02				
b	0.33	0.51	0.41				
b1	0.300	0.366	0.333				
b2	0.20	0.35	0.25				
С	0.23	0.33	0.277				
D	ļ	5.15 BSC)				
D1	4.85	4.95	4.90				
D2	1.40	1.60	1.50				
D3	-	-	3.98				
Е		6.15 BSC)				
E1	5.75	5.85	5.80				
E2	3.56 3.76		3.66				
е	1.27BSC						
k	-	-	1.27				
k1	0.56	0.56 -					
L	0.51	0.71	0.61				
La	0.51	0.71	0.61				
L1	0.05	0.05 0.20 0.4					
L4	-	0.1					
М	3.50	3.71	3.605				
х	-	-	1.400				
У	-	-	1.900				
θ	10°	12°	11°				
θ1	6°	8°	7°				
AI	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value		
Dimensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	3.910		
X2	1.650		
X3	1.650		
X4	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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